

1-Line Ultra Low Capacitance Uni-directional TVS Diode

Description

The PESDR3301P1L is an uni-directional TVS diode, to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high--speed data lines. The PESDR3301P1L has an ultra-low capacitance with a typical value at 0.6pF, and complies with the IEC61000-4-2 (ESD) standard with ±20kV air and ±20kV contact discharge. It is assembled into an ultra-small 1.0x0.6x 0.5mm lead-free DFN package. The small size, ultra-low capacitance and high ESD surge protection make PESDR3301P1L an ideal choice to protect cellphone, digital video interfaces, HDMI, DVI, USB2.0, USB3.0 and other high speed ports.

Features

- Ultra low capacitance: 0.6pF
- Low operating voltage: 3.3V
- · Low clamping voltage
- 2-pin leadless package
- Complies with following standards:
 - -IEC 61000-4-2 (ESD) immunity test

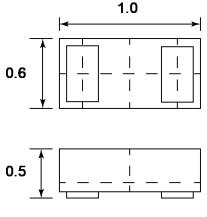
Air discharge: ±20kV

Contact discharge: ±20kV

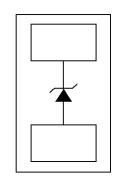
-IEC 61000-4-5 (Lightning) 4A (8/20µs)

RoHS Compliant

Dimensions and Pin Configuration







Circuit and Pin Schematic

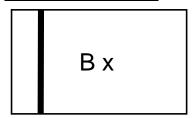
Mechanical Characteristics

- Package: DFN1006-2 (1.0×0.6×0.5mm)
- Case Material: "Green" Molding Compound.
- Moisture Sensitivity: Level 1 per J-STD-020
- Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Display Ports
- MDDI Ports
- USB Ports
- Digital Video Interface (DVI)
- PCI Express and Serial SATA Ports

Marking Information



B x = Device Marking Code Bar denotes cathode

Ordering Information

Part Number	Shipping	Reel Size
PESDR3301P1L	10000/Tape & Reel	7 inch



Absolute Maximum Ratings (TA=25°C unless otherwise specified)

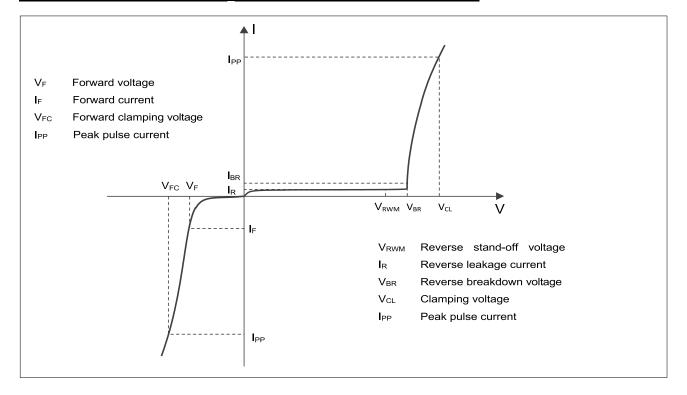
Parameter	Symbol	Value	Unit	
Peak Pulse Power (8/20µs)	РРК	56	W	
Peak Pulse Current (8/20µs)	IPP	4	А	
ESD per IEC 61000-4-2 (Air)	V	±20	kV	
ESD per IEC 61000-4-2 (Contact)	V _{ESD}	±20		
Lead temperature	TL	260	C	
Operating Temperature Range	Тор	-40 ~ + 85	C	
Storage Temperature Range	Tstg	−55 ~ + 150	°C	

Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			3.3	V	
Breakdown Voltage	V_{BR}	4.0	4.5		V	I _T = 1mA
Reverse Leakage Current	I _R			0.1	μA	V _{RWM} = 3.3V
Clamping Voltage	Vc			10	V	I _{PP} = 1A (8/20µs pulse),
Clamping Voltage	Vc			14	V	I _{PP} = 4A (8/20µs pulse),
Junction Capacitance	Сл		0.6		pF	V _R = 0V, f = 1MHz



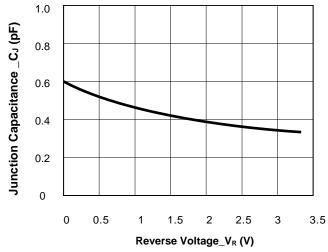
Electrical characteristics (TA = 25°C, unless otherwise noted)



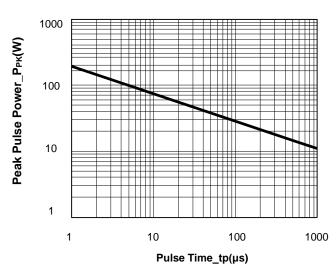
Definitions of electrical characteristics



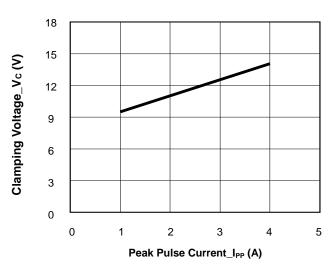
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



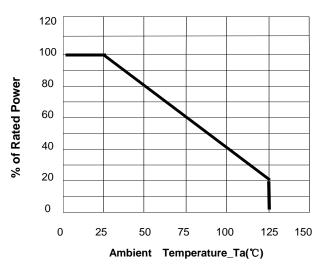
Junction Capacitance vs. Reverse Voltage



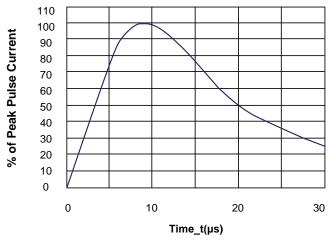
Peak Pulse Power vs. Pulse Time



Clamping Voltage vs. Peak Pulse Current



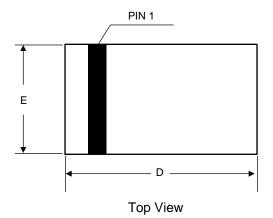
Power Derating Curve

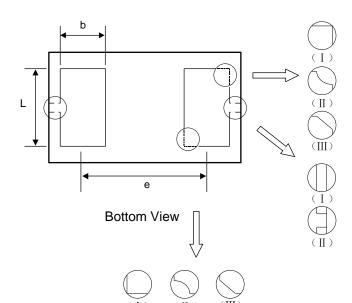


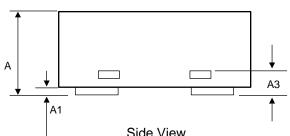
8/20µs Pulse Waveform



DFN1006-2 Package Outline Drawing



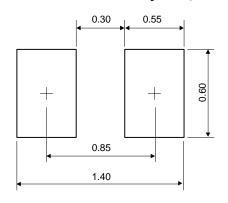




<u> </u>		A3
A 1		<u> </u>
	Side View	ı
	Symbol	

Complete	Dimensions in Millimeters				
Symbol	Min.	Тур.	Max.		
А	0.340	0.450	0.550		
A1	0.000	0.000 0.020			
A3		0.125 Ref.			
D	0.950	1.000	1.075		
E	0.490	0.600	0.675		
b	0.200	0.250	0.300		
L	0.450 0.500 0.550		0.550		
е		0.650 BSC			

Recommended PCB Layout (Unit: mm)



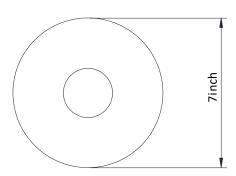
Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.

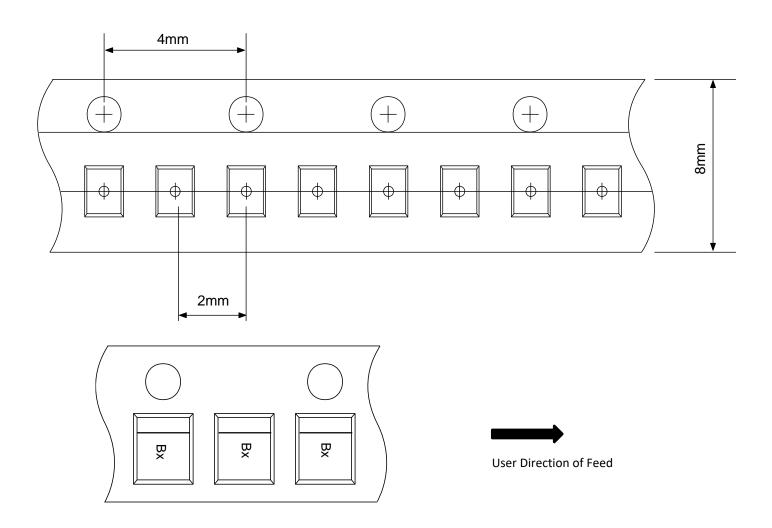


TAPE AND REEL INFORMATION





Tape Dimensions





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